

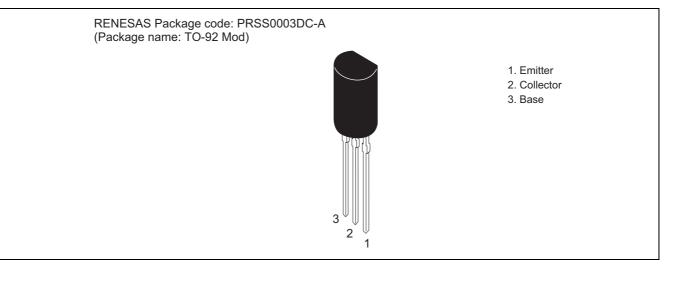
Silicon PNP Epitaxial

REJ03G1504-0200 Rev.2.00 Mar 05, 2007

Features

- Low frequency power amplifier
- Complementary pair with HIT667

Outline



Absolute Maximum Ratings

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	-120	V
Collector to emitter voltage	V _{CEO}	-100	V
Emitter to base voltage	V _{EBO}	-6	V
Collector current	Ι _C	-1.0	A
Collector peak current	I _{C (peak)} * ¹	-2.0	A
Collector power dissipation	Pc	0.9	W
Junction temperature	Тј	150	°C
Storage temperature	Tstg	-55 to +150	°C

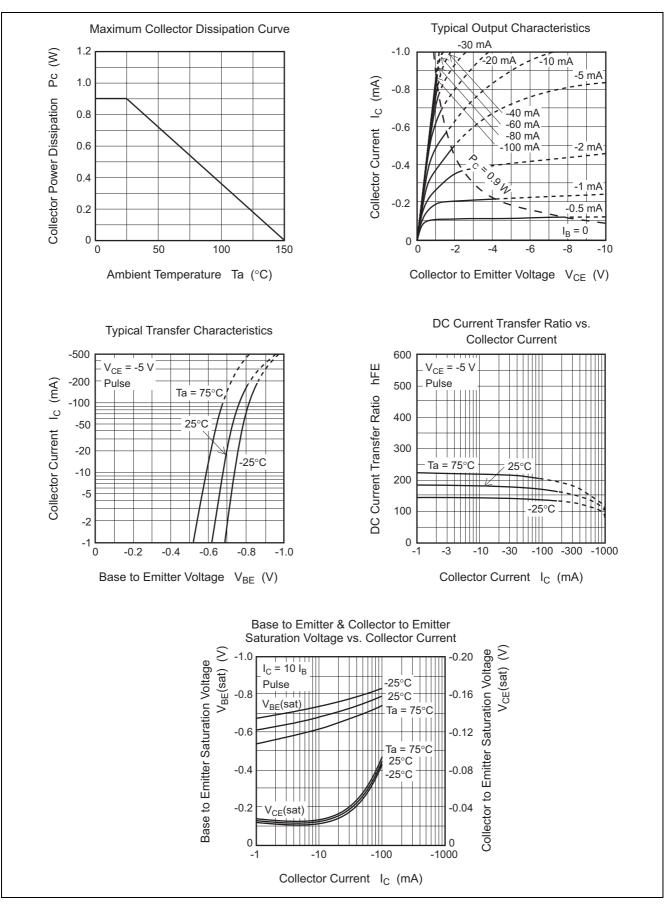
Note : 1. PW \leq 10 ms, Duty cycle \leq 20%



Electrical Characteristics

						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	V _{(BR)CBO}	-120		—	V	$I_{C} = -100 \ \mu A, I_{E} = 0$
Collector to emitter breakdown voltage	V _{(BR)CEO}	-100		—	V	I_{C} = -10 mA, R_{BE} = ∞
Emitter to base breakdown voltage	V _{(BR)EBO}	-6	_	—	V	$I_E = -100 \ \mu A, \ I_C = 0$
Collector cutoff current	I _{CBO}	—	_	-500	nA	$V_{CB} = -120 \text{ V}, I_E = 0$
Emitter cutoff current	I _{EBO}	—	_	-500	nA	$V_{EB} = -6 V, I_{C} = 0$
DC current transfer ratio	h _{FE1}	140	_	350	_	$V_{CE} = -2 V, I_C = -150 mA$
	h _{FE2}	40	_	—	_	$V_{CE} = -5 V, I_C = -1 A$
Collector to emitter saturation voltage	V _{CE(sat)}	_		-0.5	V	$I_{\rm C}$ = -500 mA, $I_{\rm B}$ = -50 mA
Base to emitter saturation voltage	V _{BE(sat)}	—	—	-1.1	V	$I_{C} = -500 \text{ mA}, I_{B} = -50 \text{ mA}$

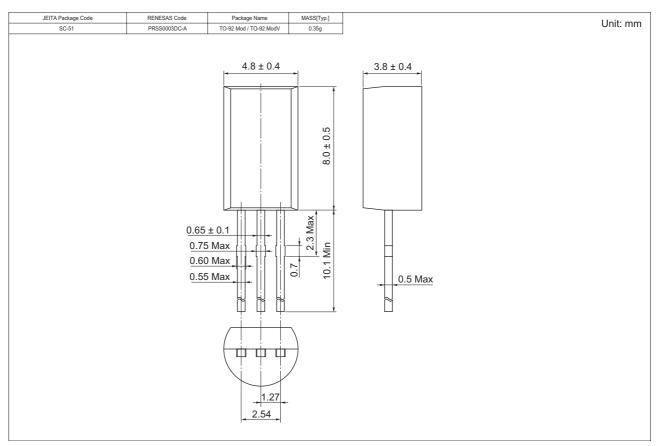




Main Characteristics



Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
HIT647-EQ	2500 pcs	Bulk, Vinyl Bag
HIT647TZ-EQ	2500 pcs	Hold Box, Radial Taping

Note: This product is designed for consumer use and not for automotive.



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